

## 8Mb LOW VOLTAGE,

## ULTRA LOW POWER PSEUDO CMOS STATIC RAM

### Features

- High-Speed access time :
  - 70ns ( IS66WV51216EALL )
  - 60ns (IS66/67WV51216EBLL )
- CMOS Lower Power Operation
- Single Power Supply
  - VDD =1.7V~1.95V( IS66WV51216EALL )
  - VDD =2.5V~3.6V (IS66/67WV51216EBLL )
- Three State Outputs
- Data Control for Upper and Lower bytes
- Lead-free Available

### DESCRIPTION

The /SS/ IS66WV51216EALL and IS66/67WV51216EBLL are high-speed,8M bit static RAMs organized as 512K words by 16 bits. It is fabricated using /SS's high performance CMOS technology.

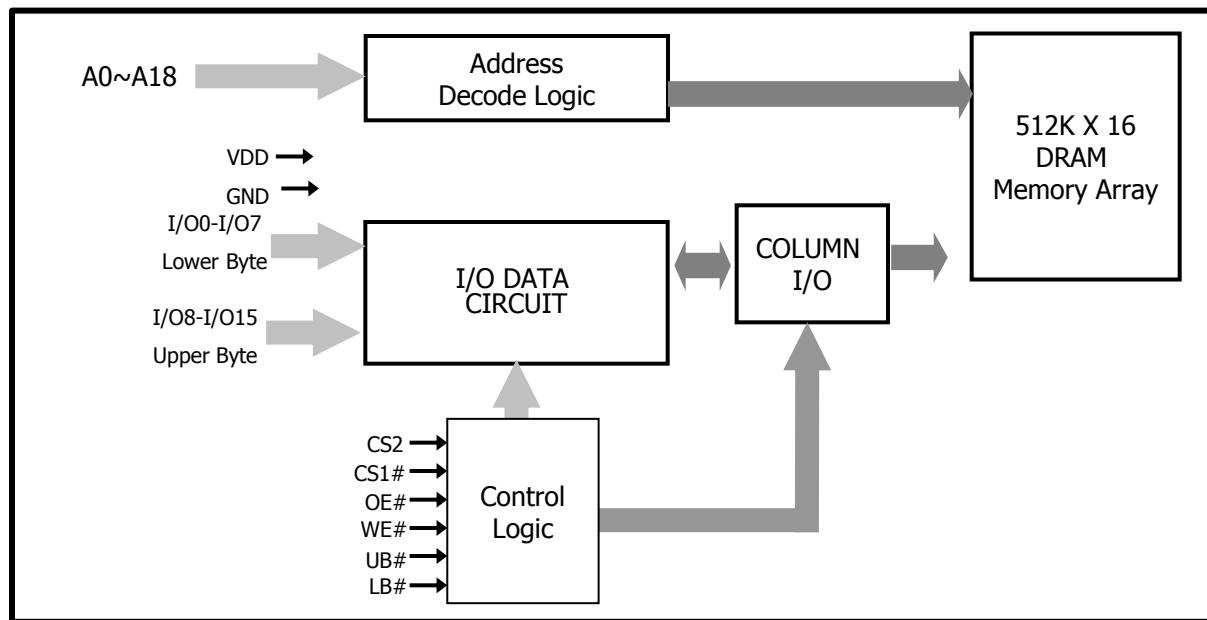
This highly reliable process coupled with innovative circuit design techniques, yields high-performance and low power consumption devices.

When CS1# is HIGH (deselected) or when CS2 is LOW (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

Easy memory expansion is provided by using Chip Enable and Output Enable inputs. The active LOW Write Enable (WE#) controls both writing and reading of the memory. A data byte allows Upper Byte (UB#) and Lower Byte (LB#) access.

The IS66WV51216 EALL and IS66/67WV51216EBLL are packaged in the JEDEC standard 48-ball mini BGA (6mm x 8mm) and 44-Pin TSOP(TYPE-II). The device is also available for die sales.

### FUNCTIONAL BLOCK DIAGRAM



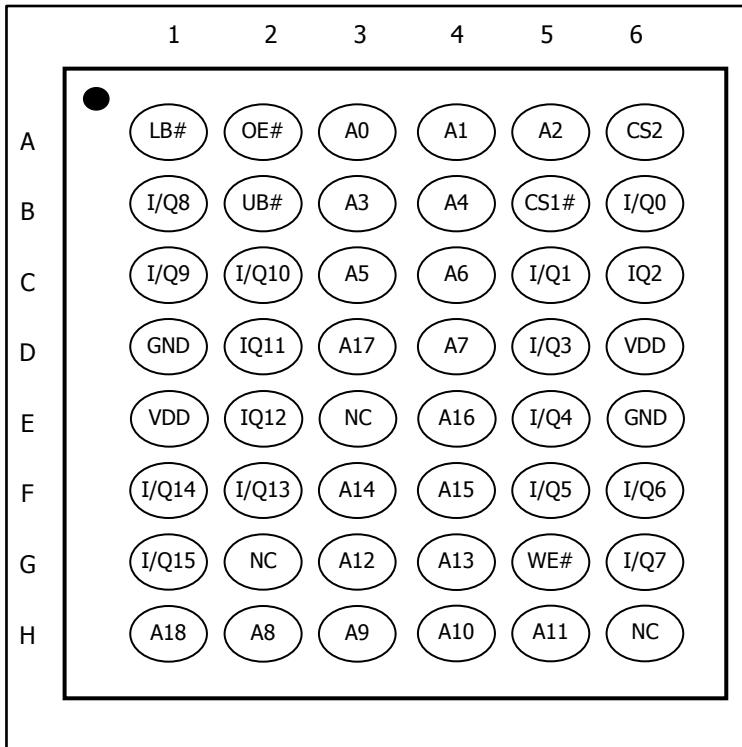
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- a.) the risk of injury or damage has been minimized;
- b.) the user assume all such risks; and
- c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

## PIN CONFIGURATIONS

### 48-Ball miniBGA (6mm x 8mm) Ball Assignment



### 44-pin TSOP (Type II)

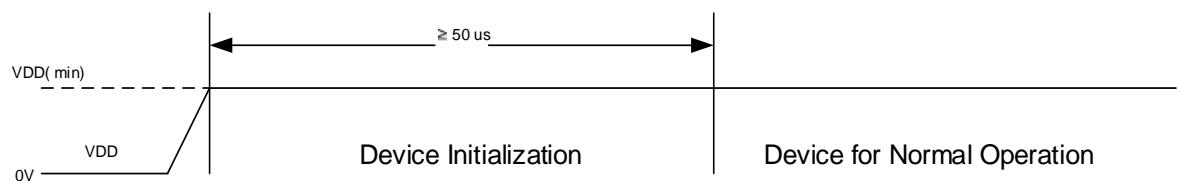
A4	1	44	A5
A3	2	43	A6
A2	3	42	A7
A1	4	41	OE#
A0	5	40	UB#
CS1#	6	39	LB#
I/O0	7	38	I/O15
I/O1	8	37	I/O14
I/O2	9	36	I/O13
I/O3	10	35	I/O12
VDD	11	34	GND
GND	12	33	VDD
I/O4	13	32	I/O11
I/O5	14	31	I/O10
I/O6	15	30	I/O9
I/O7	16	29	I/O8
WE#	17	28	A18
A16	18	27	A8
A15	19	26	A9
A14	20	25	A10
A13	21	24	A11
A12	22	23	A17

## PIN DESCRIPTIONS

Symbol	Type	Description
A0~A18	Input	Address Inputs
I/Q0~I/Q15	Input / Output	Data Inputs/Outputs
CS1#, CS2	Input	Chip Enable
OE#	Input	Output Enable
WE#	Input	Write Enable
UB#	Input	Upper Byte select
LB#	Input	Lower Byte select
VDD	Power Supply	Power
GND	Power Supply	Ground

## POWER UP INITIALIZATION

IS66WV51216EALL and IS66/67WV51216EBLL include an on-chip voltage sensor used to launch the power-up initialization process. When VDD reaches a stable level at or above the VDD (min) the device will require 50µs to complete its self-initialization process. During the initialization period, CS1# should remain HIGH. When initialization is complete, the device is ready for normal operation.



## TRUTH TABLE

Mode	WE#	CS1#	CS2	OE#	LB#	UB#	I/O0 – I/O7	I/O8 – I/O15	VDD Current
Not Selected	X X	H X	X L	X X	X X	H X	High-Z High-Z	High-Z High-Z	ISB1,ISB2 ISB1,ISB2
Output Disabled	H H	L L	H H	H H	L X	X L	High-Z High-Z	High-Z High-Z	ICC ICC
Read	H H H	L L L	H H H	L L L	L H L	H L L	DOUT High-Z DOUT	High-Z DOUT DOUT	ICC ICC ICC
Write	L L L	L L L	H H H	X X X	L H L	H L L	Din High-Z Din	High-Z Din Din	ICC ICC ICC

### Notes:

CS2 input signal pin is only available for 48-ball mini BGA package part. CS2 input is internally enabled for 44-pin TSOP II package part.

## OPERATING RANGE (VDD)

Range	Ambient Temperature	<b>IS66WV51216EALL (70ns)</b>	<b>IS66WV51216EBLL (55ns, 70ns)</b>	<b>IS66WV51216EBLL (55ns, 70ns)</b>
Industrial	–40°C to +85°C	1.7V – 1.95V	2.5V – 3.6V	–
Automotive , A1	–40°C to +85°C	–	–	2.5V – 3.6V
Automotive , A2	–40°C to +105°C	–	–	2.5V – 3.6V

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND	-0.2 to VDD + 0.3	V
TBIAS	Temperature Under BIAS	-40 to +85	°C
VDD	VDD Related to GND	-0.2 to +3.8	V
TSTG	Storage Temperature	-65 to +150	°C
PT	Power Dissipation	1.0	W

**Notes:**

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**DC ELECTRICAL CHARACTERISTICS (Over Operating Range)**
**VDD = 2.5V-3.6V (IS66/67WV51216EBLL)**

Symbol	Parameter	Test Conditions	VDD	Min.	Max.	Unit
VOH	Output HIGH Voltage	IOH = -1 mA	2.5-3.6V	2.2	—	V
VOL	Output LOW Voltage	IOL = 2.1 mA	2.5-3.6V	—	0.4	V
VIH	Input HIGH Voltage <sup>(1)</sup>		2.5-3.6V	2.2	VDD + 0.3	V
VIL	Input LOW Voltage <sup>(1)</sup>		2.5-3.6V	-0.2	0.6	V
ILI	Input Leakage	GND ≤ VIN ≤ VDD		-1	1	µA
ILO	Output Leakage	GND ≤ VOUT ≤ VDD, Outputs Disabled		-1	1	µA

**Notes:**

1. VILL (min.) = -2.0V AC (pulse width < 10ns). Not 100% tested.  
VIHH (max.) = VDD + 2.0V AC (pulse width < 10ns). Not 100% test

**DC ELECTRICAL CHARACTERISTICS (Over Operating Range)**
**VDD = 1.7V-1.95V (IS66WV51216EALL)**

Symbol	Parameter	Test Conditions	VDD	Min.	Max	Unit
VOH	Output HIGH Voltage	IOH = -0.1 mA	1.7-1.95V	1.4	—	V
VOL	Output Low Voltage	IOL = 0.1 mA	1.7-1.95V	—	0.2	V
VIH	Input HIGH Voltage <sup>(1)</sup>		1.7-1.95V	1.4	VDD + 0.2	V
VIL	Input Low Voltage <sup>(1)</sup>		1.7-1.95V	-0.2	0.4	V
ILI	Input Leakage	GND ≤ VIN ≤ VDD		-1	1	µA
ILO	Output Leakage	GND ≤ VOUT ≤ VDD, Outputs Disabled		-1	1	µA

**Notes:**

1. VILL (min.) = -1.0V AC (pulse width < 10ns). Not 100% tested.  
VIHH (max.) = VDD + 1.0V AC (pulse width < 10ns). Not 100% test

## CAPACITANCE

Symbol	Description	Conditions	MIN	MAX	Unit
$C_{IN}$	Input Capacitance	$V_{IN} = 0V$	-	8	pF
$C_{IO}$	Input/Output Capacitance (DQ)	$V_{OUT} = 0V$	-	10	pF

### Notes:

- Tested initially and after any design or process changes that may affect these parameters.

## AC TEST CONDITIONS

Parameter	1.7V – 1.95V ( Unit )	2.5V – 3.6V ( Unit )
Input Pulse Level	0.4V to VDD – 0.2V	0.4V to VDD – 0.3V
Input Rise and Fall Time	5ns	5ns
Input and Output Timing and Reference Level	$V_{REF}$	$V_{REF}$
Output Load	See Figures 1 and 2	See Figures 1 and 2

Symbol	1.7V – 1.95V	2.5V – 3.6V
$R_1(\Omega)$	3070	1029
$R_2(\Omega)$	3150	1728
$V_{REF}$	0.9V	1.4V
$V_{TM}$	1.8V	2.8V

## AC TEST LOADS

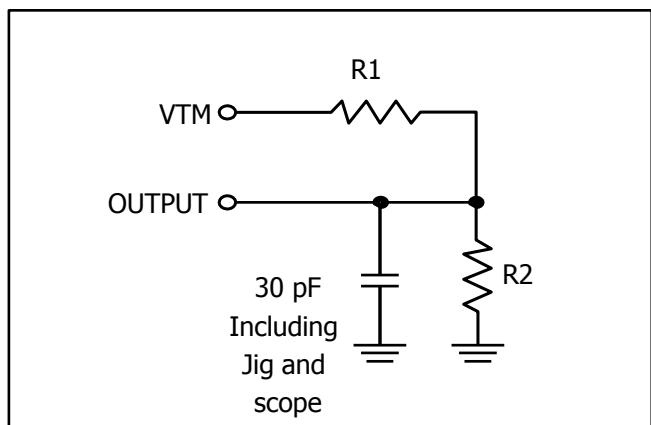


Figure 1

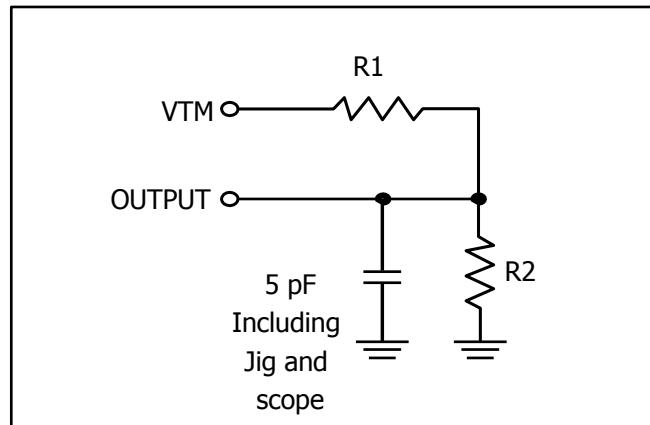


Figure 2

**1.7V-1.95V POWER SUPPLY CHARACTERISTICS (Over Operating Range)**

<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Device</b>	<b>TYP.</b>	<b>MAX. 70ns</b>	<b>Unit</b>
I <sub>cc</sub>	VDD Dynamic Operating Supply Current	V <sub>DD</sub> =Max., I <sub>OUT</sub> =0mA, f=f <sub>MAX</sub> , All inputs = 0.4V or V <sub>DD</sub> – 0.2V	Com. Ind. Auto	- - -	20 25 30	mA
I <sub>CC1</sub>	Operating Supply Current	V <sub>DD</sub> =Max., CS1#=0.2V, WE#= V <sub>DD</sub> – 0.2V, f=1MHz	Com. Ind. Auto	- - -	8 8 10	mA
I <sub>SB1</sub>	TTL Standby Current ( TTL Inputs )	V <sub>DD</sub> =Max., V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> , CS1#= V <sub>IH</sub> , CS2=V <sub>IL</sub> , f=1MHz	Com. Ind. Auto	- - -	0.6 0.6 1	mA
I <sub>SB2</sub>	CMOS Standby Current ( CMOS Inputs )	V <sub>DD</sub> =Max., CS1# $\geq$ V <sub>DD</sub> – 0.2V, CS2 $\leq$ 0.2V, V <sub>IN</sub> > V <sub>DD</sub> – 0.2V or V <sub>IN</sub> < 0.2V, f=0	Com. Ind. Auto	- - -	100 120 150	uA

Notes:

- At f=f<sub>MAX</sub>, address and data inputs are cycling at the maximum frequency , f = 0 means no input lines change.

**2.5V-3.6V POWER SUPPLY CHARACTERISTICS (Over Operating Range)**

<b>Symbol</b>	<b>Parameter</b>	<b>Conditions</b>	<b>Device</b>	<b>TYP</b>	<b>MAX 55ns</b>	<b>Unit</b>
I <sub>cc</sub>	VDD Dynamic Operating Supply Current	V <sub>DD</sub> =Max., I <sub>OUT</sub> =0mA, f=f <sub>MAX</sub> , All inputs = 0.4V or V <sub>DD</sub> – 0.3V	Com. Ind. Auto Typ.(2)	- - - -	25 28 35 15	mA
I <sub>CC1</sub>	Operating Supply Current	V <sub>DD</sub> =Max., CS1#=0.2V, WE#= V <sub>DD</sub> – 0.2V, f=1MHz	Com. Ind. Auto	- - -	8 8 10	mA
I <sub>SB1</sub>	TTL Standby Current ( TTL Inputs )	V <sub>DD</sub> =Max., V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> , CS1#= V <sub>IH</sub> , CS2=V <sub>IL</sub> , f=1MHz	Com. Ind. Auto	- - -	0.6 0.6 1	mA
I <sub>SB2</sub>	CMOS Standby Current ( CMOS Inputs )	V <sub>DD</sub> =Max., CS1# $\geq$ V <sub>DD</sub> – 0.2V, CS2 $\leq$ 0.2V, V <sub>IN</sub> > V <sub>DD</sub> – 0.2V or V <sub>IN</sub> < 0.2V ,f=0	Com. Ind. Auto Typ.(2)	- - - -	100 130 150 75	uA

Notes:

- At f=f<sub>MAX</sub>, address and data inputs are cycling at the maximum frequency , f = 0 means no input lines change.
- Typical values are measured at V<sub>DD</sub> = 3.0V, Ta = 25 °C , and not 100% tested.

**READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup>(Over Operating Range)**

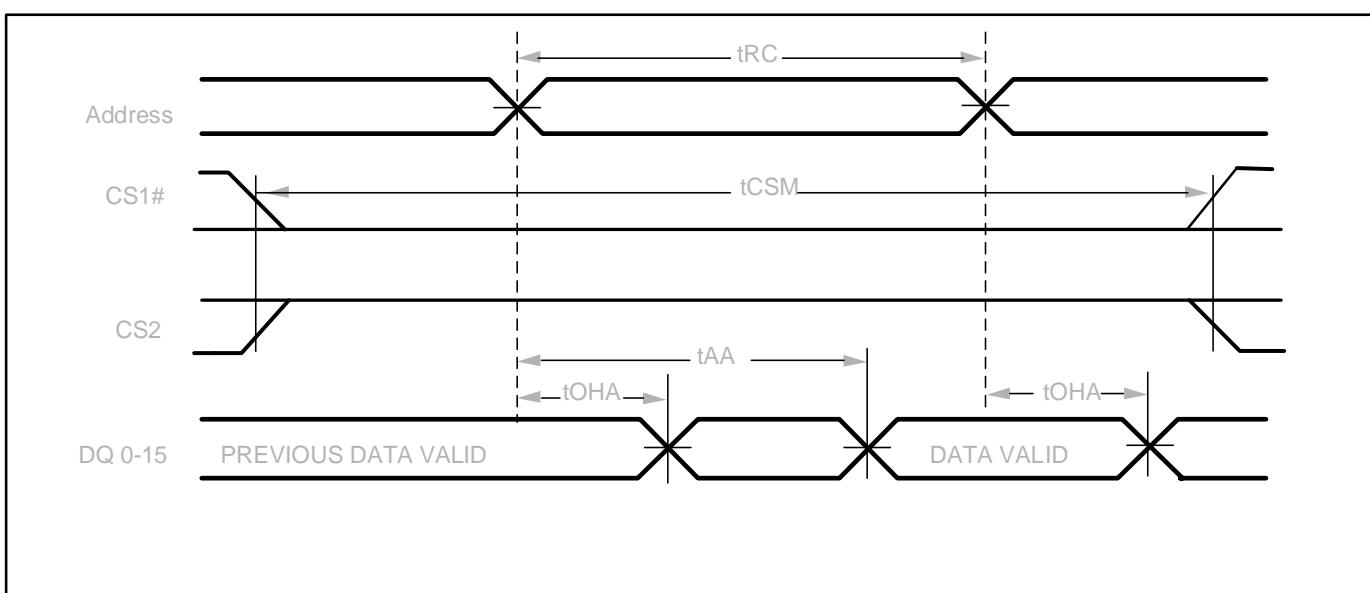
Symbol	Parameter	-55		-70		Unit	Notes
		Min	Max	Min	Max		
$t_{RC}$	Read cycle time	60	-	70	-	ns	
$t_{AA}$	Address Acess Time	-	60	-	70	ns	1
$t_{OHA}$	Output Hold Time	10	-	10	-	ns	
$t_{ACS1/ACS2}$	CS1#/CS2 Acess Time	-	60	-	70	ns	
$t_{DOE}$	OE# Access Time	-	25	-	35	ns	1
$t_{HZOE}$	OE# to High-Z output	-	20	-	25	ns	2
$t_{LZOE}$	OE# to Low-Z output	5	-	5	-	ns	2
$t_{CSM}$	Maximum CS1#/CS2 pulse width	-	15	-	15	us	
$t_{HZCS1/HZCS2}$	CS1#/CS2 to High-Z output	0	20	0	25	ns	2
$t_{LZCS1/HZCS2}$	CS1#/CS2 to Low-Z output	10	-	10	-	ns	2
$t_{BA}$	UB#/LB# Acess Time	-	60	-	70	ns	1
$t_{HZB}$	UB#/LB# to High-Z output	0	20	0	25	ns	2
$t_{LZB}$	UB#/LB# to Low-Z output	0	-	0	-	ns	2
$t_{CPH}$	CS1# HIGH (CS2 LOW) time	5	-	5	-	ns	

Notes:

1. Test conditions and output loading are specified in the AC Test Conditions and AC Test Loads (Figure 1) on page 5.
2. Tested with the load in Figure 2. Transition is measured  $\pm 100$  mV from steady-state voltage. Not 100% tested.

## AC WAVEFORMS

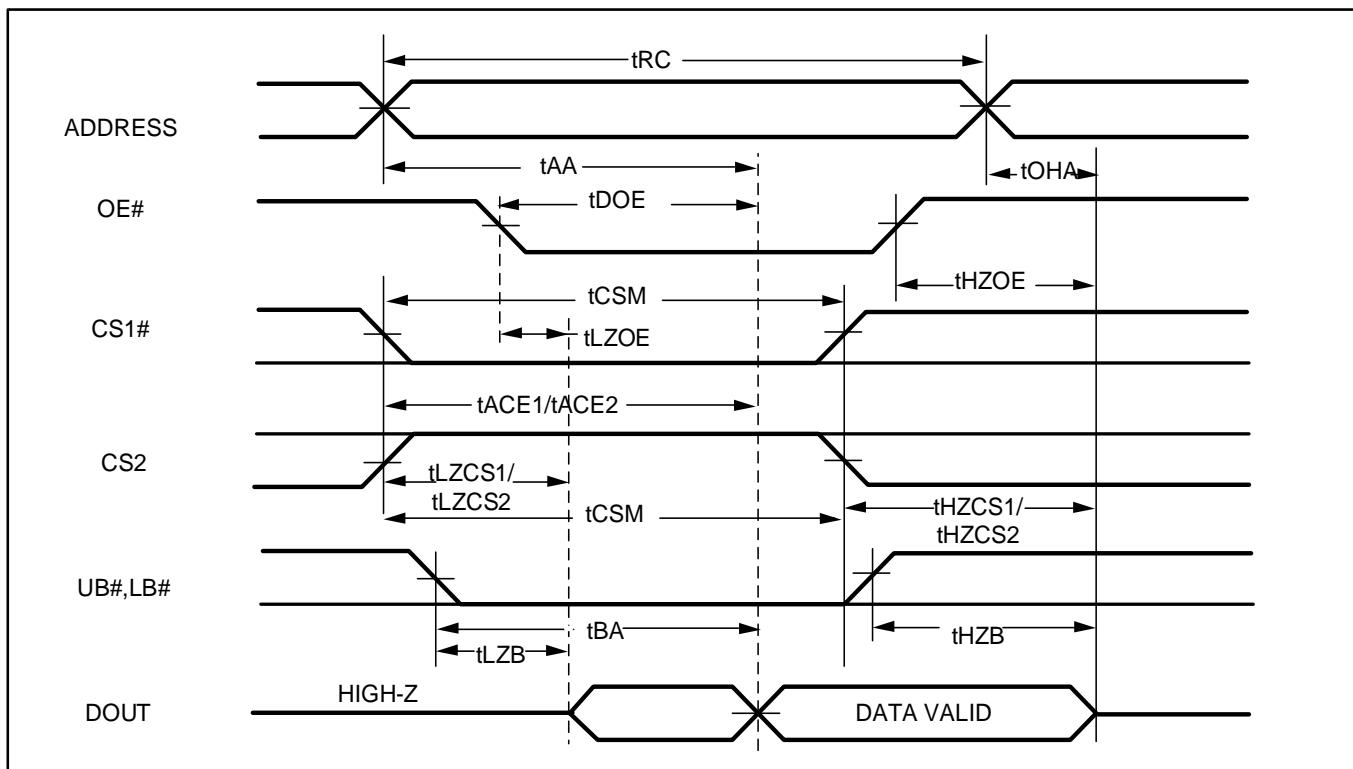
### READ CYCLE NO. 1<sup>(1)</sup> (Address Controlled, OE#=V<sub>I</sub>L, WE#=V<sub>I</sub>H, UB# or LB# = V<sub>I</sub>L)



Notes:

1. WE# is HIGH for a Read Cycle.

**READ CYCLE NO. 2<sup>(1)</sup> (CS1#, CS2, OE# and UB#/LB# Controlled)**



**Notes:**

1. Address is valid prior to or coincident with CS1# LOW (CS2 HIGH) transition, and is valid after or coincident with CS1# HI GH (CS2 LOW) transition.

**WRITE CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)**

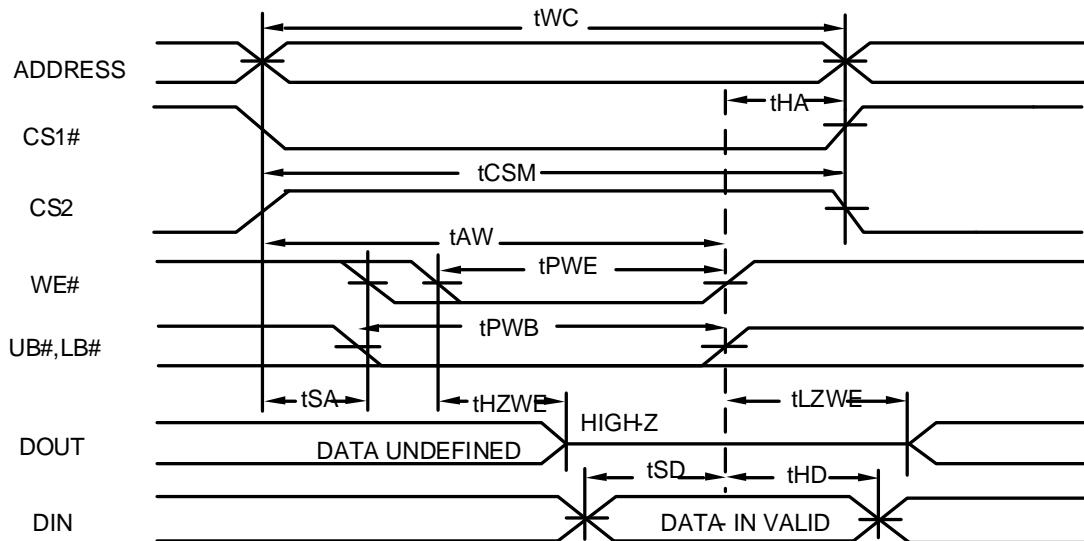
Symbol	Parameter	-55		-70		Unit	Notes
		Min	Max	Min	Max		
$t_{WC}$	Write Cycle Time	55	-	70	-	ns	
$t_{SCS1/SCS2}$	CS1#/CS2 to Write End	45	-	60	-	ns	
$t_{CSM}$	Maximum CS1#/CS2 pulse width	-	15	-	15	us	
$t_{AW}$	Address Setup to Write Time	45	-	60	-	ns	
$t_{HA}$	Address Hold to End of Write	0	-	0	-	ns	
$t_{SA}$	Address Setup Time	0	-	0	-	ns	
$t_{PWB}$	UB#/LB# Valid to End of Write	45	-	60	-	ns	
$t_{PWE}$	WE# Pulse Width	45	-	60	-	ns	
$t_{SD}$	Data Setup Time	25	-	30	-	ns	
$t_{HZWE}$	WE# LOW to High-Z output	-	20	-	30	ns	3
$t_{LZWE}$	WE# HIGH to Low-Z output	5	-	5	-	ns	3
$t_{CPH}$	CS1# HIGH (CS2 LOW) time	5	-	5	-	ns	

Notes:

1. Test conditions and output loading are specified in the AC Test Conditions and AC Test Loads (Figure 1) on page 5.
2. The internal write time is defined by the overlap of CS1#, UB#, LB# and WE# LOW, CS2 HIGH . All signals must be in valid states to initiate a Write, but anyone can go inactive to terminate Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signals that terminates the Write.
3. Tested with the load in Figure 2. Transition is measured  $\pm 100$  mV from steady-state voltage. Not 100% tested.
4.  $t_{PWE} > t_{HZWE} + t_{SD}$  when OE# is LOW.
5. Chip Select Active Time (both CS1# LOW and CS2 HIGH) must not be longer than tCMS of 15 us.

## AC WAVEFORMS

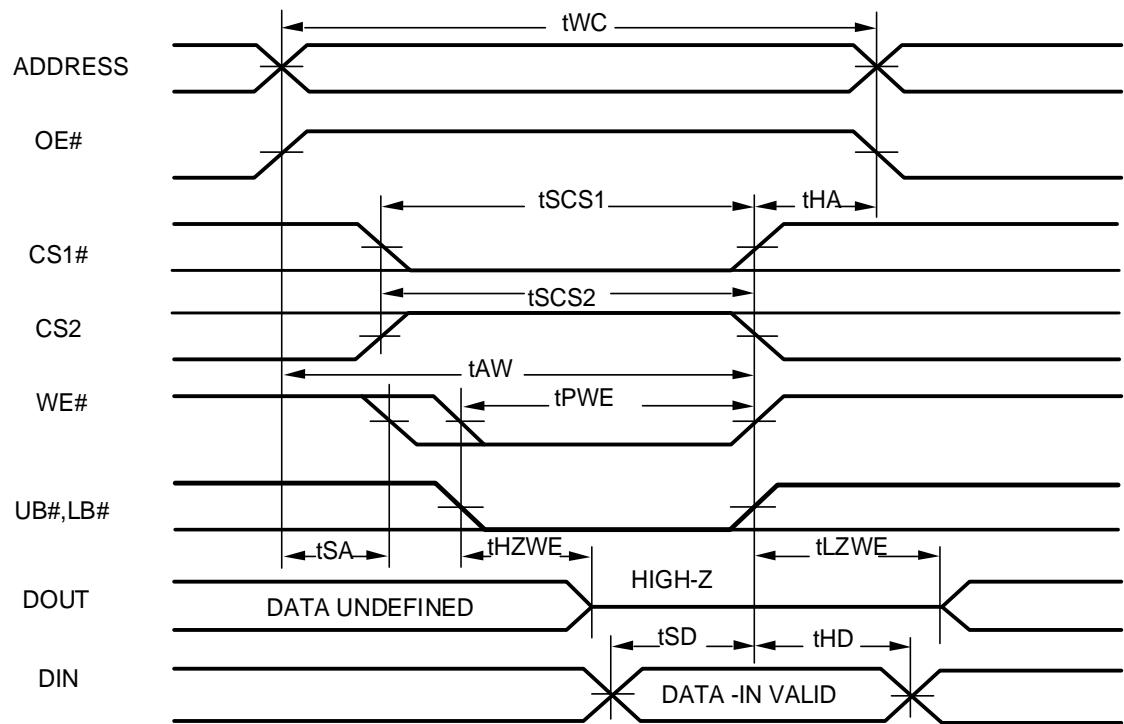
### WRITE CYCLE NO. 1<sup>(1)</sup> (CS1# Controlled, OE#= HIGH or LOW)



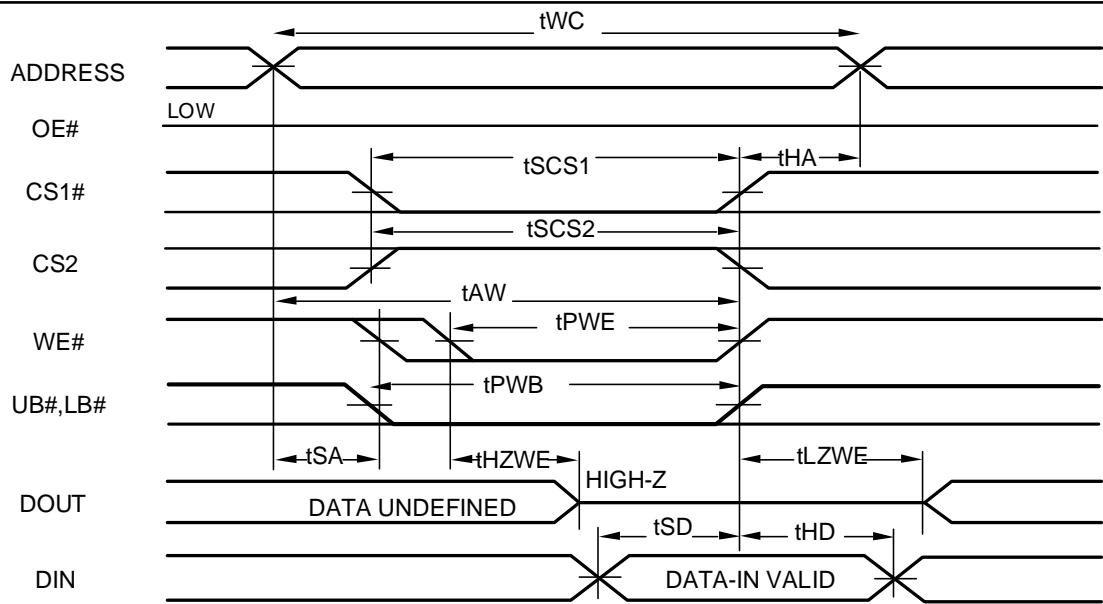
#### Notes:

1. Write address is valid prior to or coincident with CS1# LOW (CS2 HIGH) transition, and is valid after or coincident with CS1# HIGH (CS2 LOW) transition.

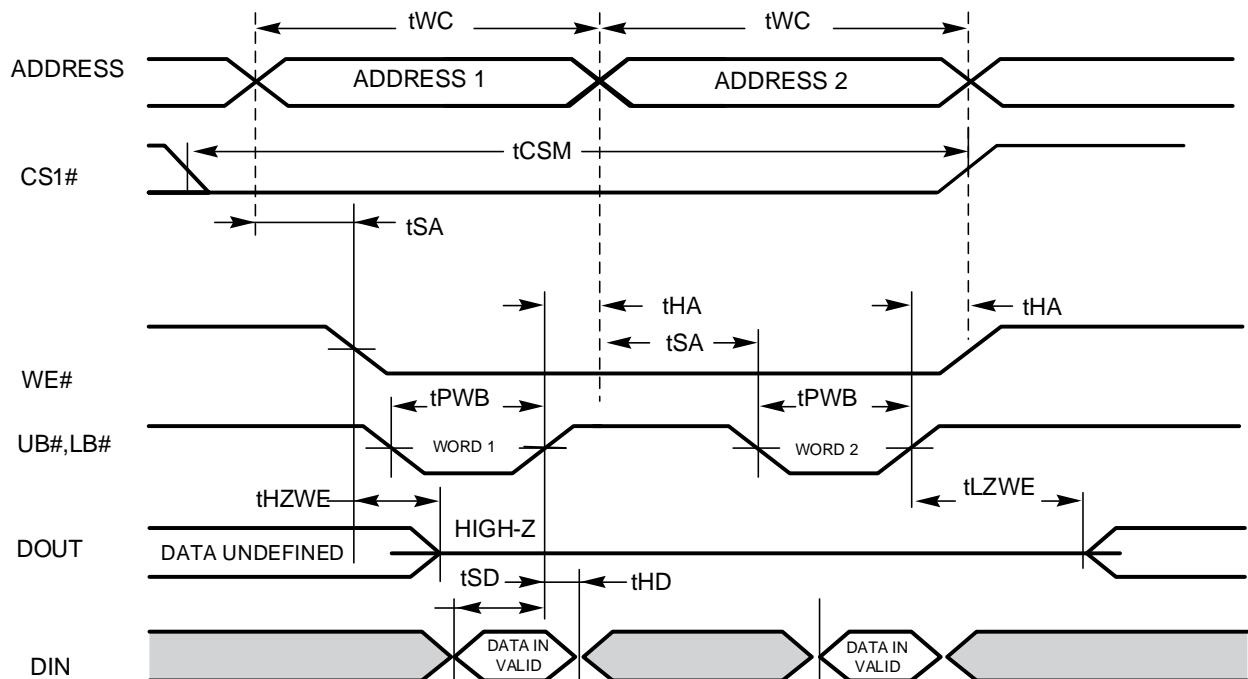
### WRITE CYCLE NO. 2 (WE# Controlled, OE#= HIGH during Write Cycle)



**WRITE CYCLE NO. 3 (WE# Controlled, OE#= LOW during Write Cycle)**

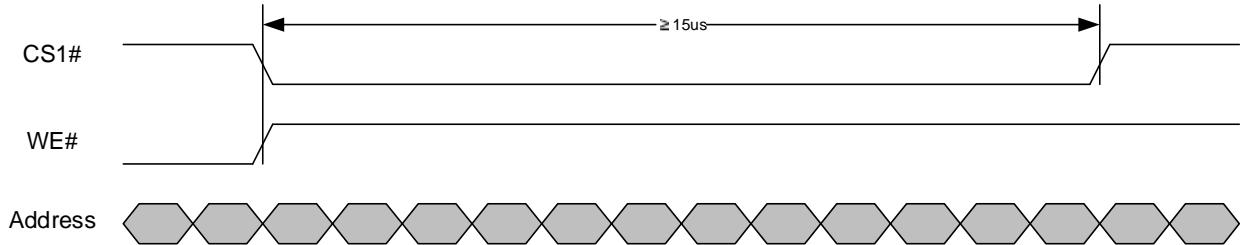


**WRITE CYCLE NO. 4 (UB# / LB# Controlled, CS2 is HIGH during Write Cycle)**

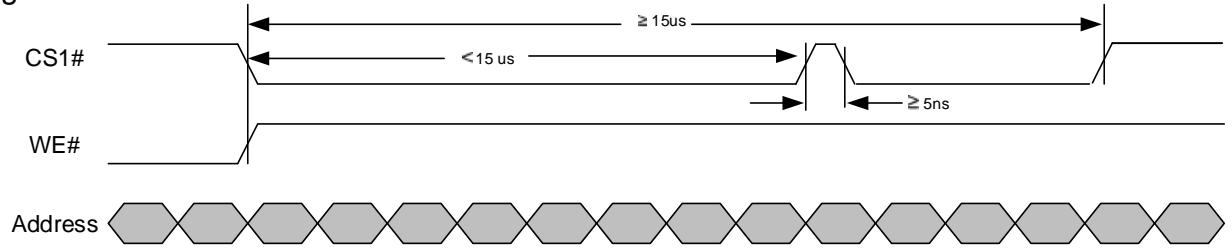


## AVOIDABLE TIMING and RECOMMENDATIONS

**Figure 3a : tCSM Violation**



**Figure 3b : Recommendation**



## AVOIDABLE TIMING and RECOMMENDATIONS

Figure 4a : tCSM Violation

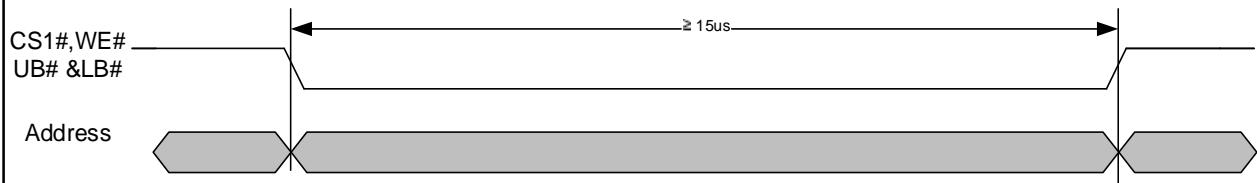
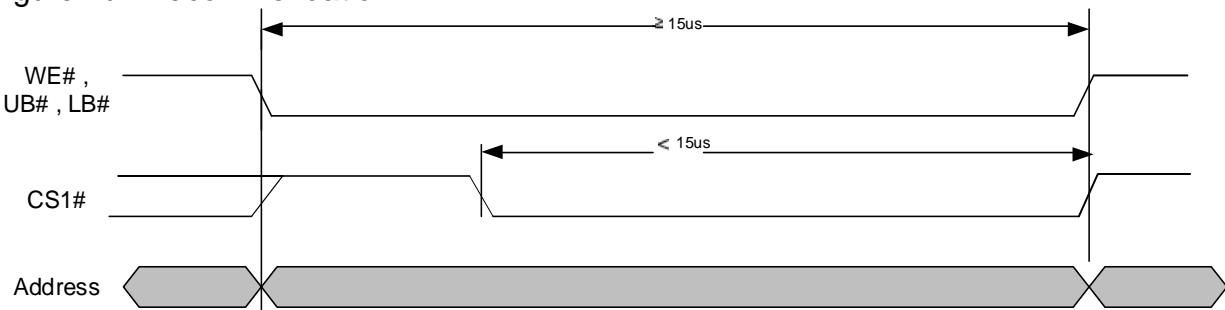


Figure 4b : Recommendation



### Notes:

1. PSRAM uses DRAM cell which needs a REFRESH action periodically to retain the information. This REFRESH action is performed only when the device is not selected (Chip Select Pins are Disabled). A hidden REFRESH action has to be executed by the device at least once every  $15\mu s$  of tCSM.
  2. Figure 3a shows a timing example in which consecutive READ cycles for more than  $15\mu s$ . This timing should be avoided for proper REFRESH operation.  
REFRESH operation can begin only during Chip Select pins are Disabled (CS1# is High and CS2 is Low ) for more than 5ns. Example on how to avoid tCSM violation in Figure 3a is shown in Figure 3b.
  3. Figure 4a shows a timing example in which a single WRITE operation is maintained for a period greater than  $15\mu s$ . Since a proper REFRESH action cannot be performed during device is selected by Chip Select pins, information stored in the device will not be retained if this timing occurs.
- Figure 4b is a timing example of using CS1# signal toggling for proper the WRITE operation

### **IS66WV51216EALL**

**Industrial Temperature Range: (-40°C to +85°C)**

**Voltage Range : 1.7V to 1.95V**

Config.	Speed (ns)	Order Part No.	Package
512K x16	70	IS66WV51216EALL-70TLI IS66WV51216EALL-70BLI	TSOP-II, Lead-free mini BGA(6mm x 8mm), Lead-free

### **IS66WV51216EBLL**

**Industrial Temperature Range: (-40°C to +85°C)**

**Voltage Range : 2.5V to 3.6V**

Config.	Speed (ns)	Order Part No.	Package
512K x16	55	IS66WV51216EBLL-55TLI IS66WV51216EBLL-55BLI	TSOP-II, Lead-free mini BGA(6mm x 8mm), Lead-free
	70	IS66WV51216EBLL-70TLI IS66WV51216EBLL-70BLI	TSOP-II, Lead-free mini BGA(6mm x 8mm), Lead-free

### **IS67WV51216EBLL**

**Automotive (A1) Temperature Range: (-40°C to +85°C)**

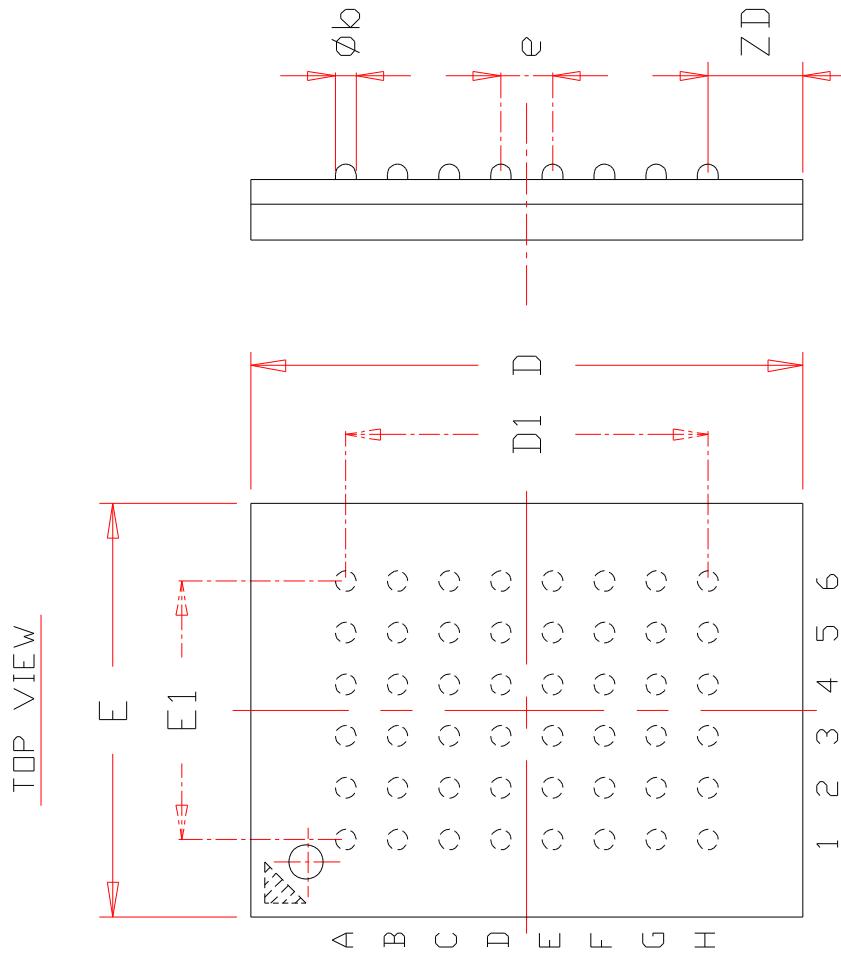
**Voltage Range : 2.5V to 3.6V**

Config.	Speed (ns)	Order Part No.	Package
512K x16	55	IS67WV51216EBLL-55TLA1 IS67WV51216EBLL-55BLA1	TSOP-II, Lead-free mini BGA(6mm x 8mm), Lead-free
	70	IS67WV51216EBLL-70TLA1 IS67WV51216EBLL-70BLA1	TSOP-II, Lead-free mini BGA(6mm x 8mm), Lead-free

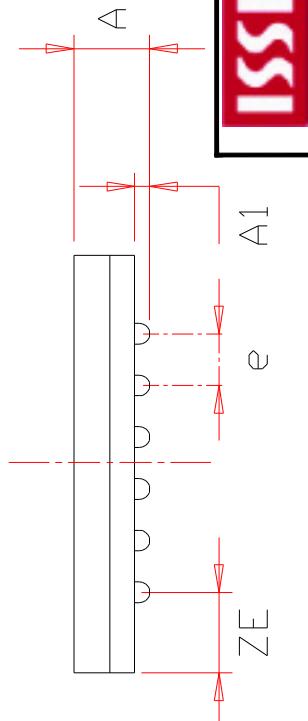
Notes :

1. Please contact ISSI SRAM marketing at [sram@issi.com](mailto:sram@issi.com) if you need -40 °C to +105 °C product.

SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A		1.20			0.047	
A1	0.20		0.30	0.008		0.012
Øb	0.30	0.35	0.40	0.012	0.014	0.016
D	7.90	8.00	8.10	0.311	0.315	0.319
D1	5.25	BSC		0.207	BSC	
E	5.90	6.00	6.10	0.232	0.236	0.240
E1	3.75	BSC		0.148	BSC	
e	0.75	BSC,		0.030	BSC,	
ZD	1.375	REF.		0.054	REF.	
ZE	1.125	REF.		0.044	REF.	

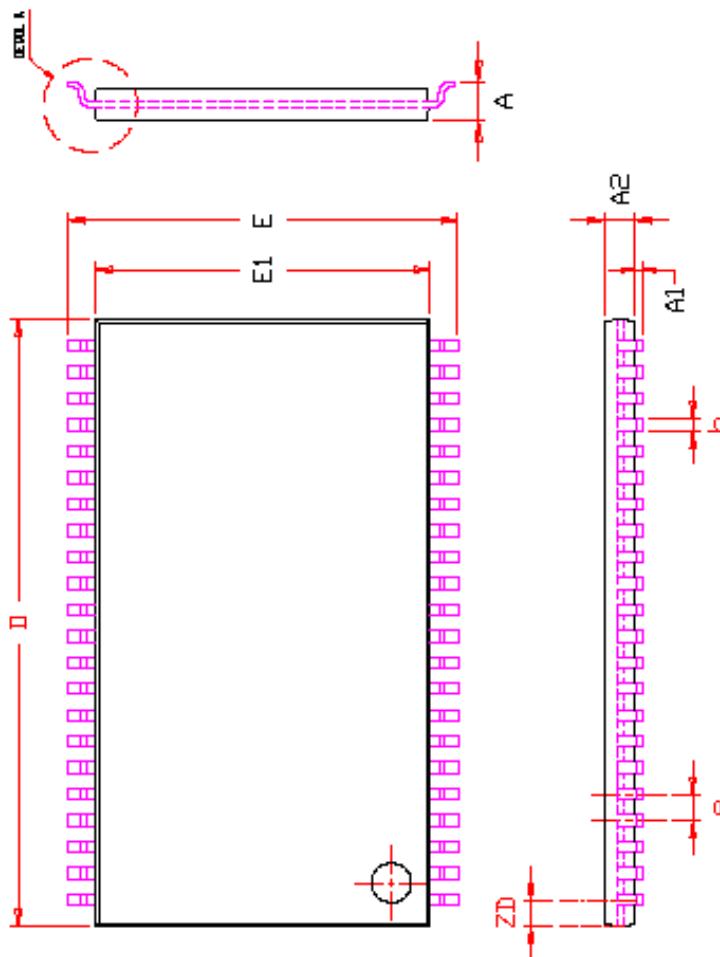

**NOTE :**

1. CONTROLLING DIMENSION : MM .
2. Reference document : JEDEC MO-207



<b>ISSI</b>	TITLE	48L 6x8mm TF-BGA Package Outline	REV.	C	DATE	08/12/2008
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SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.20	0.039	0.047		
A1	0.05	0.15	0.002	0.006		
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30	0.45	0.012	0.018		
D	18.28	18.41	18.54	0.720	0.725	0.730
E	11.56	11.76	11.96	0.4550	0.4630	0.471
E1	10.03	10.16	10.29	0.3950	0.4000	0.405
e	0.80	BSC.		0.031	BSC.	
L	0.40		0.69	0.016		0.027
L1	0.25	BSC.		0.010	BSC.	
ZD	0.805	REF.		0.032	REF.	
②	0		8°	0		8°



**NOTE :**

1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.

ISSI	TITLE	44L 400mil TSOP-2	REV.	F	DATE
		Package Outline			06/04/2008